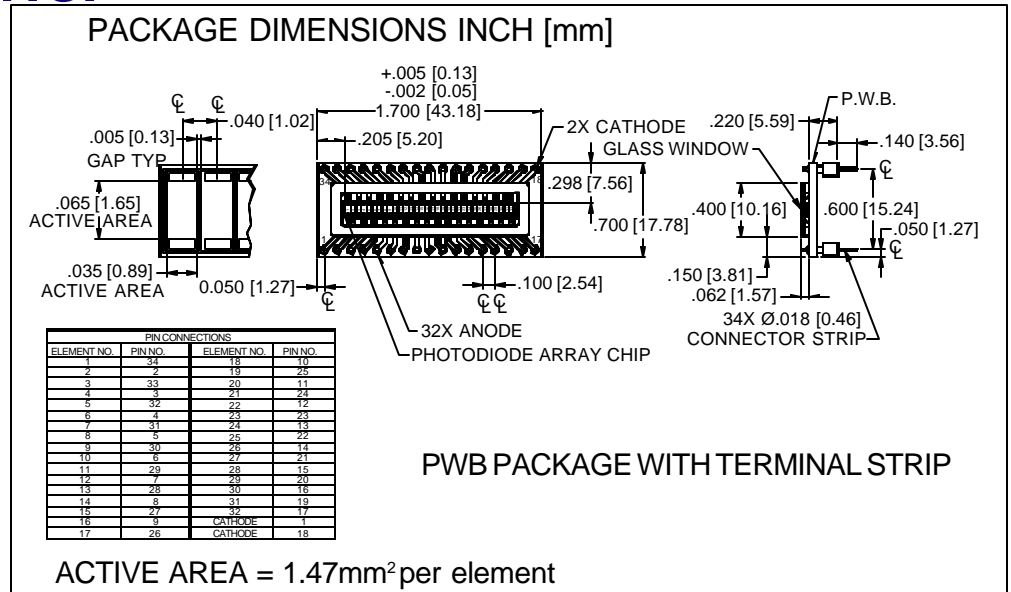
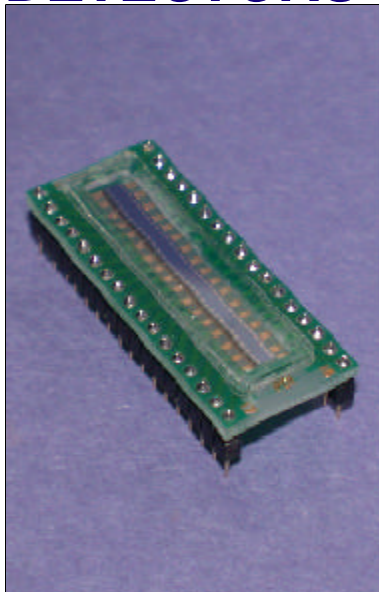


PHOTONIC DETECTORS INC.

Silicon Photodiode Array, Photovoltaic 32 Element Type PDB-V232



FEATURES

- .100 inch centers
- Uniform outputs (\pm 5%)
- Blue enhanced
- Low crosstalk (\pm 2%)

DESCRIPTION

The **PDB-V232** is a common cathode, monolithic silicon PIN photodiode linear array. Packaged on a custom P.C.B. substrate, with dual .100 inch center terminal strips.

APPLICATIONS

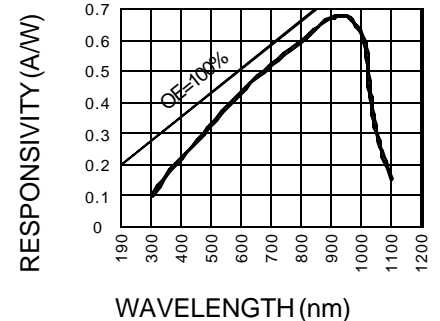
- Card reader
- Scanners
- Character recognition

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V _{BR}	Reverse Voltage		50	V
T _{STG}	Storage Temperature	-50	+100	°C
T _O	Operating Temperature Range	-40	+75	°C
T _S	Soldering Temperature*		+265	°C
I _L	Light Current		0.5	mA

*1/16 inch from case for 3 secs max

SPECTRAL RESPONSE



ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I _{SC}	Short Circuit Current	H = 100 fc, 2850 K	7.5	10		μA
I _D	Dark Current	H = 0, V _R = 5 V		200	400	pA
R _{SH}	Shunt Resistance	H = 0, V _R = 10 mV	250	500		MΩ
TCR _{SH}	RSH Temp. Coefficient	H = 0, V _R = 10 mV		-8		% / °C
C _J	Junction Capacitance	H = 0, V _R = 0 V**		180		pF
λ _{range}	Spectral Application Range	Spot Scan	350		1100	nm
λ _p	Spectral Response - Peak	Spot Scan		950		nm
V _{BR}	Breakdown Voltage	I = 10 μA	30	50		V
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		1x10 ⁻¹⁴		W/√Hz
tr	Response Time	RL = 50 Ω V _R = 10 V		200		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice. **f = 1 MHz [FORMNO. 100-PDB-V232REVB]